IN THE CLAIMS

Please replace claims 1, 3, 10, 12, and 19 with amended claims 1, 3, 10, 12, and 19 below. A marked-up version of the amended claims showing insertions and deletions is provided in Appendix A.

1. (amended) An organic field effect transistor (FET) comprising an active dielectric layer disposed on a substrate, the substrate being suitable for an organic FET, wherein the active dielectric layer comprises a film of at least one liquid-deposited silsesquioxane precursor cured at a temperature of less than about 200 °C to provide a high-dielectric strength film.

3. (amended) The organic FET of claim 1 wherein the temperature is less than about 150°C.

10. (amended) An organic field transistor (FET) comprising an active dielectric layer disposed on a substrate, the substrate being suitable for an organic (FET), wherein the active dielectric layer comprises a high-speed deposition product of at least one liquid-deposited alkyl(methyl) and alkyl(methyl) phenyl silsesquioxane precursors cured at a temperature of less than about 200 °C, and has a dielectric constant of above about 2.

12. (amended) The organic FET of claim 10 wherein the temperatures is less than about 150°C.

19. (twice amended) An article comprising an organic FET comprising:

a gate electrode on a substrate;

an active dielectric layer over the substrate;

an active semiconducting layer over the active dielectric layer, wherein the active dielectric layer comprises a high-speed deposition product of at least silsesquioxane precursor cured at a temperature of less than about 200 °C; and

a source electrode and a drain electrode in contact with the active semiconducting layer.